Advanced PECVD-Nitride2(HF n=2.00, 9.3nm/min)				Advanced PECVD Si~2700A Typical Film Properties
SiN depostion~2700A, 300C				Deposition rate=9.03nm/min
Step1:	NITRIDE2 coat			Refractive index@632.8nm=1.952
	Name	Value	Changeable	Stress=484.21MPa
	Process pressure	800 mtorr	N	HF etch rate=47.80nm/min
	RF setpoint	30 W	N	
	stabilization time	15 seconds	N	
	step time(m)	**10**	**Y**	
	step time(s)	**0**	**Y**	
	2%SiH4 %He	1040	N	
	N2	980	N	
	NH3	17	N	
Step2:	NITRIDE2 deposition			
	Name	Value	Changeable	
	Process pressure	800 mtorr	N	
	RF setpoint	30 W	N	
	stabilization time	15 seconds	N	
	step time(m)	**30**	**Y**	
	step time(s)	**0**	**Y**	
	2%SiH4 %He	1040	N	
	N2	980	N	
	NH3	17	N	
Step3: STANDARD PLASMA CLEAN				
	1. pump down			
	Name	Value	Changeable	
	stabilization time	15 seconds	N	
	step time(m)	0	N	
	step time(s)	30	N	
	2. Pre-purge			
	Name	Value	Changeable	
	purge	**1 (Yes/No)**	N	
	stabilization time	15 seconds	N	
	step time(m)	**1**	**N**	
	step time(sec)	0	N	
	3.1 High Pressure			
	Name	Value	Changeable	
	Cload position	**50%**	**N**	
	Ctune position	**50%**	**N**	
	DriveMatch	**1 (Yes/No)**	**N**	
	Process pressure	600 mtorr	N	
	RF setpoint=300	300 W	N	
	Stabilization time	35 seconds	N	
	step time(m)	**ENTER TIME**	Y	**For 7min(coat+deposition) run 1min CLEAN**
	step time(s)	0	Y	
	CF4/O2(5)	500 sccm	N	